

LAST - [10711700.wsp:1]

Drafts
 BRS: 55
 Pending
 Active
 Failed
 "Ag" "As" "C" "Cd" "Cl" "Co" "Cr" "Fe" "In" "Mg
 6946188.pn. and polycarbonate and polyester

S1: (3553) 257/758.ccis.
 S3: (0) S1 and (impure near copper)
 S4: (413) (impure near copper)
 S5: (9985) dual near damascene
 S6: (798) electroplated near copper near (plate film layer)
 S7: (131) S5 and S6
 S8: (3563) 257/758.ccis.
 S9: (8) S8 and S7
 S10: (8) S9 and (@ad<"20040930" @rlad<"20040930")
 S11: (35603677) "Ag" "As" "C" "Cd" "Cl" "Co" "Cr" "Fe" "In" "
 S12: (34839725) (silver "Ag") (Arsenic "As") (Indium "In") (le
 S13: (797) S6 and S12
 S14: (131) S13 and S5
 S15: (8) S14 and S8
 S16: (8) S15 and (@ad<"20040930" @rlad<"20040930")
 S17: (131) S14 and (@ad<"20040930" @rlad<"20040930")
 S18: (34865157) (silver "Ag") (Arsenic "As") (Indium "In") (le

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 Check for updates daily
 S21 and (@ad<"20040930" @rlad<"20040930")

	Document ID	Issue Date	Pages	Title	Current OR	Current Xref	Retrieval C	Inventor	S	C	D	B	E	2
1	US 609068 A	20000530	18	Sub-quarter-micron copper interconnections with	438/628	257/E21.584; 257/E21.585;		Rathore; Hazara S. et al.	<input checked="" type="checkbox"/>					
2	US 609069 A	20000718	9	Method to improve the adhesion of a molding	438/617	257/E21.585; 257/E21.589;		Jang; Syun-Ming et al.	<input checked="" type="checkbox"/>					
3	US 6096648 A	20000801	10	Copper/low dielectric interconnect formation with	438/687	257/E21.576; 257/E21.58;		Lopatin; Sergey et al.	<input checked="" type="checkbox"/>					
4	US 6123825 A	20000926	15	Electromigration-resistant copper microstructure and	205/183	205/118; 205/184;		Uzoh; Cyprian E. et al.	<input checked="" type="checkbox"/>					
5	US 6126806 A	20001003	17	Enhancing copper electromigration resistance	205/182	205/157; 205/170;		Uzoh; Cyprian E.	<input checked="" type="checkbox"/>					
6	US 6130161 A	20001010	14	Method of forming copper interconnections with	438/687	257/751; 257/E21.584;		Ashley; Leon et al.	<input checked="" type="checkbox"/>					
7	US 6197688 B1	20010306	13	Interconnect structure in a semiconductor device and	438/678	257/E21.175; 257/E21.584;		Simpson; Cindy Reidsema	<input checked="" type="checkbox"/>					
8	US 6235406 B1	20010522	15	Copper film including laminated impurities	428/620	205/157; 205/228;		Uzoh; Cyprian E.	<input checked="" type="checkbox"/>					
9	US 6258710 B1	20010710	18	Sub-quarter-micron copper interconnections with	438/628	257/E21.584; 257/E21.585;		Rathore; Hazara S. et al.	<input checked="" type="checkbox"/>					
10	US 6268291 B1	20010731	15	Method for forming electromigration-resistant	438/694	257/E21.175; 257/E21.575;		Andricacos; Panayotis Constantinou et al.	<input checked="" type="checkbox"/>					
11	US 6274008 B1	20010814	20	Integrated process for copper via filling	204/192.17	204/192.12; 204/192.15;		Gopalraja; Praburam et al.	<input checked="" type="checkbox"/>					
12	US 6277249 B1	20010821	22	Integrated process for copper via filling using a	204/192.12	204/192.15; 204/192.17;		Gopalraja; Praburam et al.	<input checked="" type="checkbox"/>					
13	US 6301227 B1	20010926	7	Cold precipitation annealing	438/601	257/E21.584;		Uzoh; Cyprian E.	<input checked="" type="checkbox"/>					

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